

# **Octal Buffers/Drivers With 3-State Outputs**

#### **General Description**

The ET74LV541V octal buffers/drivers is ideal for driving bus lines or buffer memory address registers. The device feature inputs and outputs on opposite sides of the package to facilitate printed circuit board layout.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable( $\overline{OE}$  1 or  $\overline{OE}$  2) input is high, all corresponding outputs are in the high-impedance state. The outputs provide non-inverted data when they are not in the high-impedance state.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to VCC through a pull-up resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

#### Features

- Designed for 2 to 5.5V VCC Operation
- Inputs are TTL Voltage Compatible
- Max tpd of 6ns at 5V
- Latch-Up performance > 250mA
- ESD Performance:
  - -- Human Body Model > 3000V
  - -- Charged Device Model > 2000V
- Part No. and package

Part No.	Package
ET74LV541V	TSSOP20 (6.5mm×4.4mm)

#### Applications

- Fully compliant with standards for automotive applications
- Combine normal power signals from multiple power rails

## Pin Configuration



### **Pin Function**

Pin No.	Name	Description
1	OE 1	Output Enable 1
2	A1	Input A1
3	A2	Input A2
4	A3	Input A3
5	A4	Input A4
6	A5	Input A5
7	A6	Input A6
8	A7	Input A7
9	A8	Input A8
10	GND	Ground
11	Y8	Output Y8
12	Y7	Output Y7
13	Y6	Output Y6
14	Y5	Output Y5
15	Y4	Output Y4
16	Y3	Output Y3
17	Y2	Output Y2
18	Y1	Output Y1
19	OE 2	Output Enable 2
20	VCC	Power

## **Block Diagram**



## **Functional Description**

#### **Function Table**

	Output		
OE 1	OE 2	A	Y
L	L	L	L
L	L	Н	Н
Н	Х	Х	Z
Х	Н	Х	Z

*Note*: H = High voltage level ,

L = Low voltage level ,

X = Don't care ,

Z = High-impedance OFF-state.

### Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage range	-0.5 to 7.0	V
VI	Input voltage range <sup>(1)</sup>	-0.5 to 7.0	V
Vo	Voltage range applied to any output in the high-impedance or power-off state <sup>(1)</sup>	-0.5 to 7.0	V
	Output voltage range applied in the high or low state $^{(1)}$ $^{(2)}$	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current, V <sub>I</sub> < GND	-20	mA
l <sub>ок</sub>	Output clamp Current, V <sub>O</sub> < GND	-50	mA
lo	Continuous output current, $I_O(V_O=0 \text{ to } V_{CC})$	±35	mA
Icc	Continuous current through V <sub>CC</sub>	±70	mA
	Continuous current through GND	±70	mA
T <sub>JMAX</sub>	Maximum Junction Temperature	150	°C
PD	Max Power Dissipation (TSSOP20)	400	mW
T <sub>STG</sub>	Storage Temperature Range	-65 to 150	°C
N/	Human Body Model ESD (JESD22-A114)	±3000	V
V <sub>ESD</sub>	Charged Device Model ESD (JESD22-C101)	±2000	
ILU	Latch up Current Maximum Rating (JESD78E)	±250	mA

*Note1*. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

*Note2.* This value is limited to 5.5V maximum.

## **Recommended Operating Conditions**

Symbol	Para	Min	Max	Unit		
V <sub>CC</sub>	Supp	oly voltage	2.0	5.5	V	
		V <sub>CC</sub> =2V	1.5		V	
		V <sub>CC</sub> =2.3V to 2.7V	V <sub>cc</sub> *0.7			
Vih	High-level input voltage	V <sub>CC</sub> =3V to 3.6V	V <sub>cc</sub> *0.7			
		V <sub>CC</sub> =4.5V to 5.5V	V <sub>cc</sub> *0.7			
		V <sub>CC</sub> =2V		0.5	V	
N		V <sub>CC</sub> =2.3V to 2.7V		V <sub>cc</sub> *0.3		
VIL	Low-level input voltage	V <sub>CC</sub> =3V to 3.6V		V <sub>CC</sub> *0.3		
		V <sub>CC</sub> =4.5V to 5.5V		V <sub>CC</sub> *0.3		
Vı	Inpu	ıt Voltage	0	5.5	V	
Vo	Outp	ut Voltage	0	Vcc	V	
-	High-level output current	V <sub>CC</sub> =2V		-50	uA	
		V <sub>CC</sub> =2.3V to 2.7V		-2	mA	
I <sub>ОН</sub>		V <sub>CC</sub> =3V to 3.6V		-8	mA	
		V <sub>CC</sub> =4.5V to 5.5V		-16	mA	
		V <sub>CC</sub> =2V		50	uA	
		V <sub>CC</sub> =2.3V to 2.7V		2	mA	
IOL	Low-level output current	V <sub>CC</sub> =3V to 3.6V		8	mA	
		V <sub>CC</sub> =4.5V to 5.5V		16	mA	
T <sub>A</sub>	Operating Ter	nperature Range	-40	125	°C	
		V <sub>CC</sub> =2.3V to 2.7V		200		
Δt/Δv	Input Transition	V <sub>CC</sub> =3V to 3.6V		100	ns/V	
	rise or fall rate	V <sub>CC</sub> =4.5V to 5.5V		20	1	

## **Electrical Characteristics**

### **DC Electrical Characteristics**

Symbol	Parameter	Condition			Т <sub>А</sub> =25°С −40		-40°C≤T	−40°C≤T <sub>A</sub> ≤125°C	
Symbol	Parameter	Condition	V <sub>cc</sub> (V)	Min	Тур	Max	Min	Max	Unit
		I <sub>он</sub> =-50uA	2 to 5.5	Vcc-0.1	4.5		Vcc-0.1		
	High-Level	I <sub>он</sub> =-2mA	2.3	2			2		v
V <sub>он</sub>	Output Voltage	I <sub>он</sub> =-8mA	3	2.48			2.48		V
		Іон=-16mA	4.5	3.8			3.8		
		I <sub>oL</sub> =50uA	2 to 5.5			0.1		0.1	
Max	Low-Level	l <sub>o∟</sub> =2mA	2.3			0.4		0.4	v
Vol	Output Voltage	l <sub>o∟</sub> =8mA	3			0.44		0.44	
		I <sub>OL</sub> =16mA	4.5			0.55		0.55	
lı	Input Leakage Current	V <sub>I</sub> =5.5V or GND	0 to 5.5			±1		±1	
l <sub>oz</sub>	Output Leakage Current	Vo=V <sub>CC</sub> or GND	5.5			±5		±5	uA
Icc	Quiescent Supply Current	V <sub>I</sub> = V <sub>CC</sub> or GND	5.5			20		20	μA
l <sub>off</sub>	Power-off Leakage Current	$V_1$ or $V_0 = 0$ to 5.5V	0			5		5	uA
Ci	VI=VCC or	GND	3.3		2				pF

## Switching Characteristics <sup>(3)</sup>

Symbol	Condition		T <sub>A</sub> =2	25°C	−40°C≤T <sub>A</sub> ≤125°C			Unit
Symbol	Conc		Тур	Max	Min	Тур	Max	Unit
		V <sub>CC</sub> =2.5V	6.7	11.3	1.0		13.5	
	From A to Y, C∟=15pF	V <sub>CC</sub> =3.3V	4.8	7.0	1.0		8.5	
+.	CL-TSPF	V <sub>CC</sub> =5V	3.5	5	1.0		6	
t <sub>pd</sub>	From A to V	V <sub>CC</sub> =2.5V	8.7	15.9	1.0		18.5	
	From A to Y, C∟=50pF	V <sub>CC</sub> =3.3V	6.1	10.5	1.0		12	
	CL-SOPF	V <sub>CC</sub> =5V	4.3	7.0	1.0		8.0	
		V <sub>CC</sub> =2.5V	8.5	16.6	1.0		19.5	ns
	From /OE to Y, C∟=15pF	Vcc=3.3V	6.1	10.5	1.0		12.5	
L +	CL-TSPF	V <sub>CC</sub> =5V	4.3	7.2	1.0		8.5	
t <sub>en</sub>	From /OF to V	V <sub>CC</sub> =2.5V	10.5	20.7	1.0		24	
	From /OE to Y, C∟=50pF	V <sub>CC</sub> =3.3V	7.4	14	1.0		16	
	CL-SUPF	V <sub>CC</sub> =5V	5.3	9.2	1.0		10.5	

Symbol	Condition		T <sub>A</sub> =2	T <sub>A</sub> =25°C		−40°C≤T <sub>A</sub> ≤125°C		
Symbol	Cond	nion	Тур	Max	Min	Тур	Max	Unit
	From /OF to V	V <sub>CC</sub> =2.5V	8.4	13.1	1.0		15	
	From /OE to Y, C∟=15pF	Vcc=3.3V	5.8	11	1.0		12	
t <sub>dis</sub>		V <sub>CC</sub> =5V	3.9	7.5	1.0		8	
		V <sub>CC</sub> =2.5V	12.3	17.9	1.0		20	
	From /OE to Y,	V <sub>CC</sub> =3.3V	8.8	15.4	1.0		17.5	ns
	C∟=50pF	V <sub>CC</sub> =5V	5.6	8.8	1.0		10	
	V <sub>CC</sub> =2	2.5V		2			2	
T <sub>sk(o)</sub>	V <sub>CC</sub> =3.3V			1.5			1.5	
	V <sub>CC</sub> =5V			1			1	

### Switching Characteristics (Continued) <sup>(3)</sup>

*Note3.* Guaranteed by design and characterization. not a FT item.

#### Noise Characteristics<sup>(4)</sup>

#### $V_{CC}$ = 3.3 V, C<sub>L</sub> = 50pF, T<sub>A</sub> = 25°C

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.5	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>o∟</sub>		-0.4	-0.8	V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>		2.9		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.31			V
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.99	V

Note4. Characteristics are for surface-mount packages only.

#### **Operating Characteristics**<sup>(5)</sup>

T<sub>A</sub> = 25°C

Symbol	Parameter		Parameter Conditions		Тур	Unit
Cod	Power dissipation	Outputs spekled	CL = 50pF,	V <sub>CC</sub> =3.3 V	16.3	_
Cpd	capacitance	Outputs enabled	f =10 MHz	V <sub>CC</sub> =5 V	17.8	pF

*Note5.* C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

# ET74LV541V





#### Notes:

A. CL includes probe and jig capacitance.

**B**. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

**C**. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1MHz, ZO= 50  $\Omega$ , tr  $\leq$ 3ns, tf  $\leq$ 3ns.

**D**. The outputs are measured one at a time, with one input transition per measurement.

 $\boldsymbol{E}$ . t<sub>PLZ</sub> and t<sub>PHZ</sub> are the same as tdis.

 $\textbf{\textit{F}}_{. t_{PZL}}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

 $\pmb{G}_{.\ t_{PHL}}$  and  $t_{PLH}$  are the same as tpd.

*H*. All parameters and waveforms are not applicable to all devices.

## **Typical Application**



Figure 9. Typical Application Schematic

## Package Dimension

### TSSOP20



## **Revision History and Checking Table**

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2023-12-20	Initial version	Shibo	Luh	Liujy